

Amendments to the Specification:

Please replace paragraph beginning at page 11, line 14 to page 12, line 2 with the following rewritten paragraph:

-- After such deposition, there is also performed a mechanical chemical polishing of the wafer 2 using the mechanical pad assembly 412. A polishing agent or slurry may be applied to the polishing pad 402 via slurry channel 410 to polish the wafer 2. A center wall 420 ~~460~~ separating the second chamber 400 from the first chamber 300. Other conventional methods for preventing the slurry from entering the plating chamber 300 can be used in the present invention. The mechanical pad assembly 412 substantially prevents metals from becoming permanently deposited on surfaces of the wafer 2 where such a deposit is undesired, due to the polishing or rubbing action of the mechanical pad 402. Accordingly, metal, i.e. copper, is deposited in vias, trenches, and the like where desired, and is substantially prevented from being deposited in undesired areas such as the surface or field area on the wafer.--